Schottky barrier diode

RB717F

●Applications

General purpose detection
High speed switching

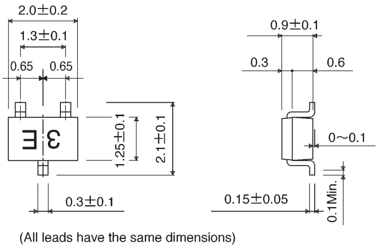
●Features

1) Multiple diodes with common anode configuration. (UMD3)
2) High reliability.
3) Low reverse current and low forward voltage.

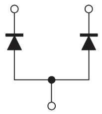
●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



(All leads have the same dimensions)



ROHM：UMD3
EIAJ：SC-70
JEDEC：SOT-323

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current *	I_{FSM}	200	mA
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40~+125	℃

* 60 Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	−	0.28	0.37	V	I_F=1mA
Reverse current	I_R	−	0.05	1	μA	V_R=10V
Capacitance between terminals	C_T	−	2.0	−	pF	V_R=1V, f=1MHz

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

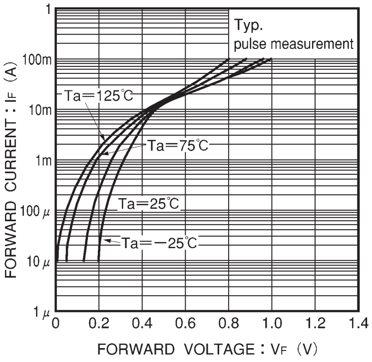


Fig. 1 Forward characteristics

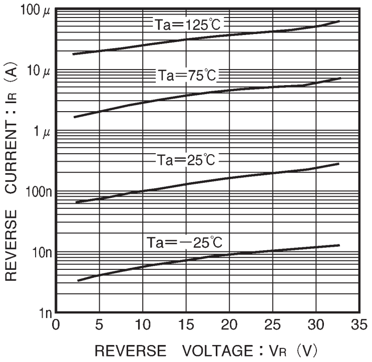


Fig. 2 Reverse characteristics

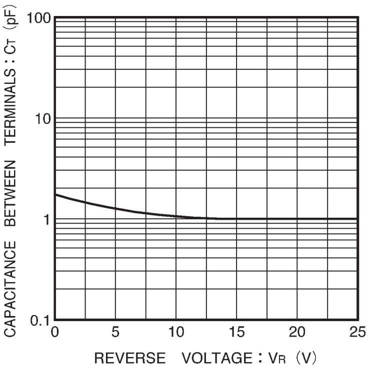


Fig. 3 Capacitance between terminals characteristics

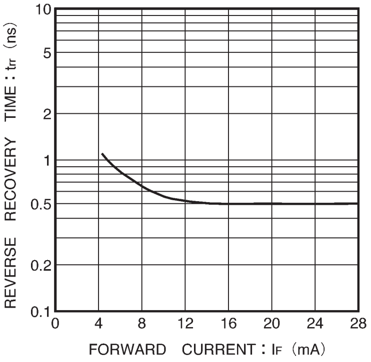


Fig. 4 Reverse recovery time characteristics

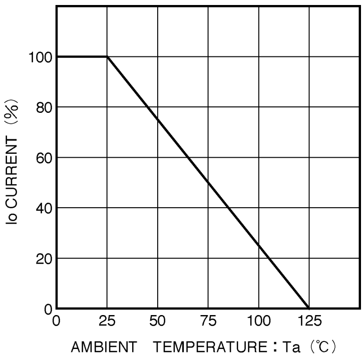


Fig.5 Power Derating
(mounting on glass epoxy PCBs)